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Tohru YAMAOKA, et al.

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	US	4,142,073	02-27-1979	AGNEUS et al.	
	US	2002/0181725 A1	12-05-2002	JOHANNSEN et al.	
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
		JP 2002-209298	07-26-2002	SEIKO EPSON CORP		JAPAN (w/English Abstract)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		United States Office Action issued in United States Patent Application No. US 10/591,456, mailed January 29, 2009.	
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		MAJAMAA, T., et al., "Effect of Oxidation Temperature on the Electrical Characteristics of Ultrathin Silicon Dioxide Layers Plasma Oxidized in Ultrahigh Vacuum", Physics Scripta, 1999, Pages 259-262, Vol. T79	
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